

FS5ASJ-06F

High-Speed Switching Use Nch Power MOS FET

REJ03G0239-0200 Rev.2.00 Dec 19, 2008

Features

• Drive voltage: 4 V

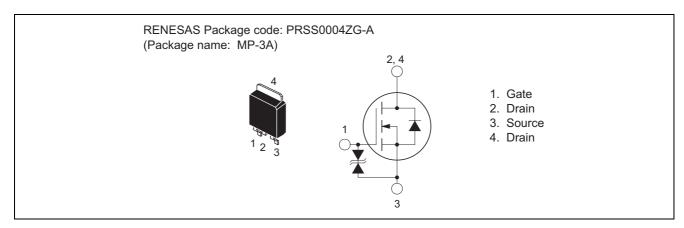
 $\bullet \quad V_{DSS}:60\;V$

• $r_{DS(ON) \, (max)}$: 140 m Ω

• I_D: 5 A

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 30 ns

Outline



Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

Maximum Ratings

 $(Tc = 25^{\circ}C)$

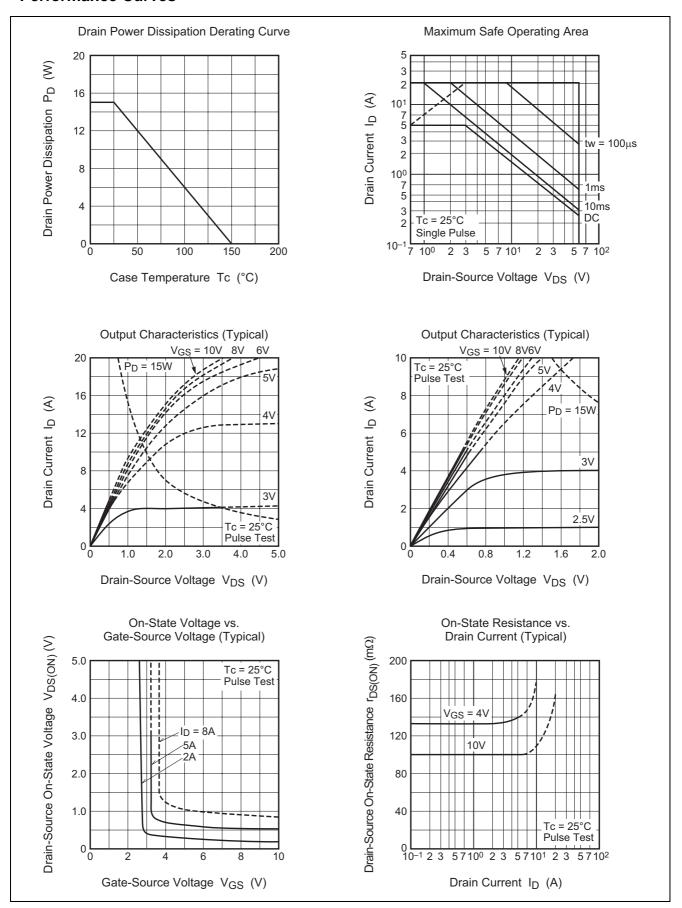
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V_{DSS}	60	V	V _{GS} = 0 V
Gate-source voltage	V_{GSS}	±20	V	$V_{DS} = 0 V$
Drain current	I _D	5	А	
Drain current (Pulse)	I _{DM}	20	А	
Avalanche current (Pulse)	I _{DA}	5	А	L = 100 μH
Source current	Is	5	А	
Source current (Pulse)	I _{SM}	20	А	
Maximum power dissipation	P _D	15	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

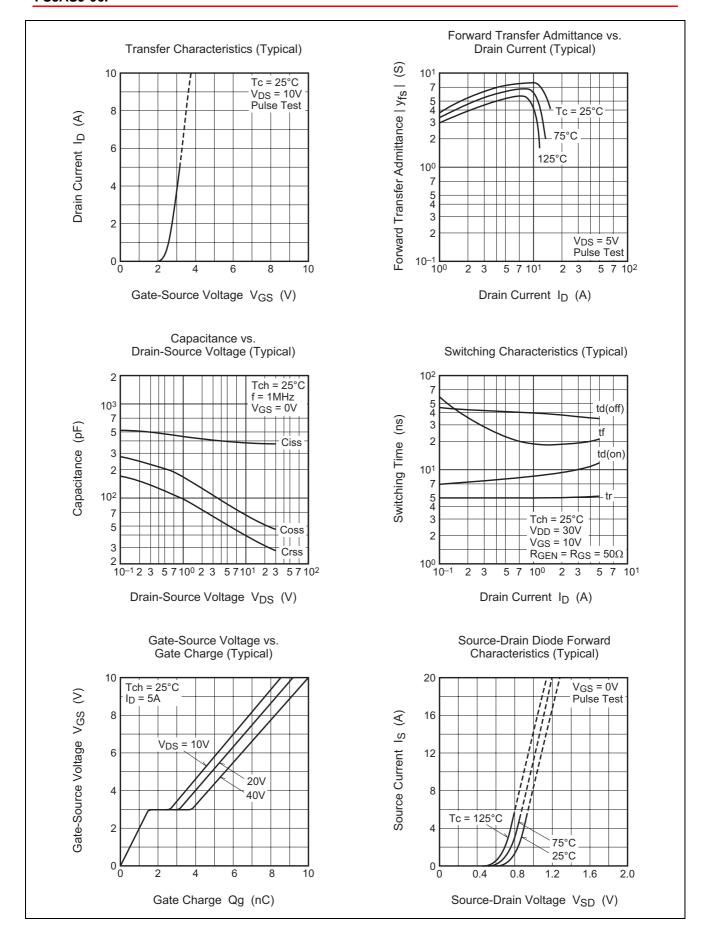
Electrical Characteristics

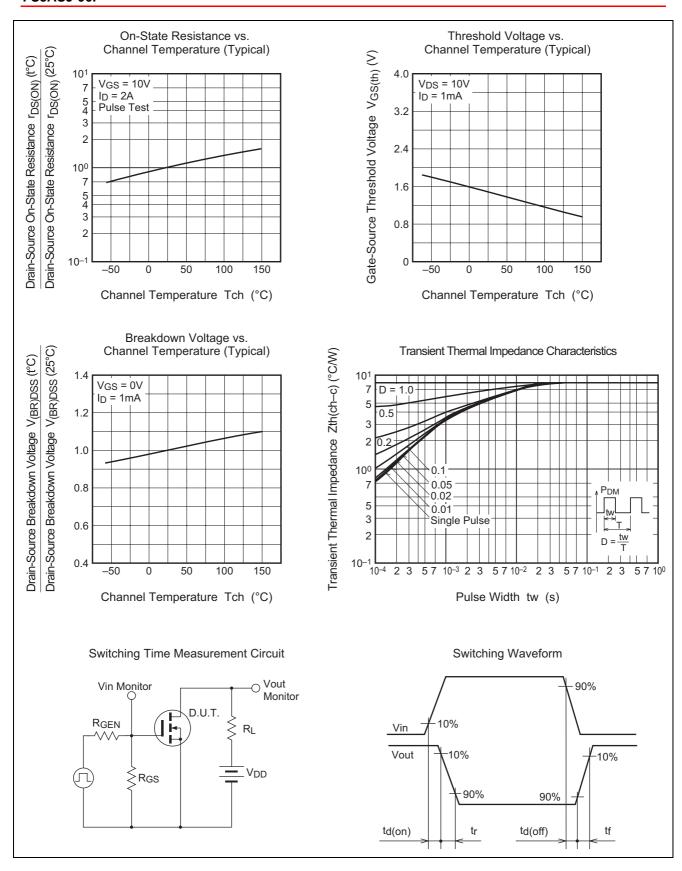
 $(Tch = 25^{\circ}C)$

(Ten = 23)						
Parameter	Symbol	Min.	TYP.	Max.	Unit	Test conditions
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	_	_	V	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}$
Gate-source breakdown voltage	V _{(BR)GSS}	±20	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0 \ V$
Drain-source leakage current	I _{DSS}	_	_	100	μΑ	$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source leakage current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Gate-source threshold voltage	V _{GS(th)}	1.0	1.5	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Drain-source on-state resistance	r _{DS(ON)}	_	110	140	mΩ	I _D = 2 A, V _{GS} = 10 V
Drain-source on-state resistance	r _{DS(ON)}	_	140	190	mΩ	$I_D = 2 A, V_{GS} = 4 V$
Drain-source on-state voltage	V _{DS(ON)}	_	0.22	0.28	V	I _D = 2 A, V _{GS} = 10 V
Forward transfer admittance	y _{fs}	_	6.0	_	S	I _D = 2 A, V _{DS} = 10 V
Input capacitance	Ciss	_	340	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	65	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	40	_	pF	
Turn-on delay time	t _{d(on)}	_	4	_	ns	$V_{DD} = 30 \text{ V}, I_D = 2 \text{ A},$
Rise time	t _r	_	10	_	ns	$V_{GS} = 10 \text{ V},$
Turn-off delay time	t _{d(off)}	_	35	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t _f	_	17	_	ns	1
Source-drain voltage	V _{SD}	_	1.0	1.5	V	I _S = 2 A, V _{GS} = 0 V
Thermal resistance	Rth(ch-c)	_	_	8.33	°C/W	Channel to case
Reverse recovery time	t _{rr}	_	30	_	ns	$I_S = 5 \text{ A}, \text{ dis/dt} = -100 \text{ A/}\mu\text{s}$

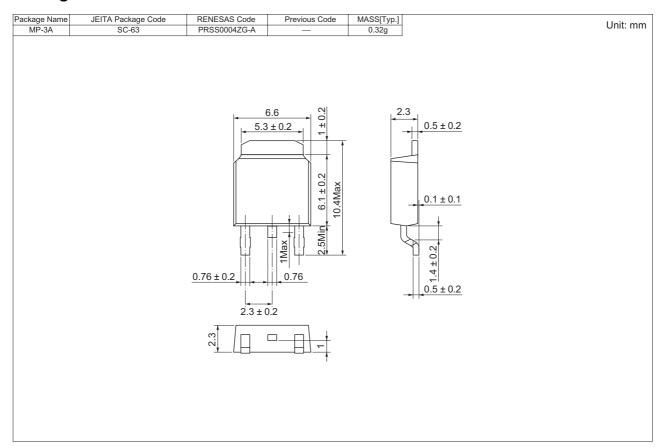
Performance Curves







Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FS5ASJ-06F-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FS5ASJ-06F

Note: Please confirm the specification about the shipping in detail.

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